EAST - text search notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1523	(strained or strain or tensile or compressive) near2 (silicon or si) near15 (sige or si near ge or gesi or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 13:30
S2	933	(strained or strain or tensile or compressive) near2 (silicon or si) near15 (sige or si near ge or gesi or silicon near germanium) and (nmos or pmos or cmos or nmosfet or pmosfet or n near mosfet or n near fet or p near mosfet or p near fet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 08:34
S3	127	(strained or strain or tensile or compressive) near2 (silicon or si) near15 (sige or si near ge or gesi or silicon near germanium) and (nmos or pmos or cmos or nmosfet or pmosfet or n near mosfet or n near fet or p near mosfet or p near fet) and gate near6 (thermal or thermally) near2 (oxide or oxidized or oxidation or oxidizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 12:28
S4	2	"6849508".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 10:57
S5	26	("20010003364" | "20010018245" | "20010039093" | "20010045582" | "20010048119" | "20010053579" | "20020008289" | "20020022376" | "20020105041" | "20020140031" | "20020160584" | "20020185686" | "20030003679" | "4471373" | "4525811" | "4806500" | "5239195" | "5442205" | "5576573" | "5723355" | "5989962" | "6025234" | "6303521" | "6429098" | "6465323" | "6472327"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/29 10:57
S6	399	(strained or strain or tensile or compressive) near2 (silicon or si) near15 (sige or si near ge or gesi or silicon near germanium) and (nmos n near fet or n near mos or n near mosfet or nmosfet) and (pmos or p near mos or p near fet or p near mosfet or pmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 14:24
S7	7	cmos and (nmos or nmosfet or n near mosfet or n near mos or n near fet) same (pmos or pmosfet or p near mosfet or p near mos or p near fet) same (balanc$4 or "same" or equal or compensated or identical or equivalent) near3 (drive or driving) near2 (current or bias or voltage) and (sige or silicon near germanium or gesi or si near ge or strained near si or strained near silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 14:26
S8	79	cmos and (nmos or nmosfet or n near mosfet or n near mos or n near fet) same (pmos or pmosfet or p near mosfet or p near mos or p near fet) same (balanc$4 or "same" or equal or compensat$4 or identical or equivalent) near3 (current or bias or voltage) and (sige or silicon near germanium or gesi or si near ge or strained near si or strained near silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 16:31
S9	99	(nmos or nmosfet or n near mosfet or n near mos or n near fet) same (pmos or pmosfet or p near mosfet or p near mos or p near fet) same (different or differing or nonuniform or dissimilar) near3 gate near (dielectric or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/29 16:59
S10	202	438/199.ccls. and (tensile or strained or strain or sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 08:59
S11	344	438/216.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 08:59

S12	995	438/275.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 09:24
S13	86	438/275.ccls. and (tensile or strained or strain or sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 09:07
S14	145	438/287.ccls. and (tensile or strained or strain or sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:10
S15	523	257/190.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:09
S16	1193	257/192.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:43
S17	375	257/192.ccls. and (tensile or strained or strain or sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:43
S18	803	257/410.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:55
S19	143	257/410.ccls. and (tensile or strained or strain or sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:43
S20	378	257/616.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 10:55
S21	31	(pmos or pmosfet or p near mos or p near mosfet or p near channel or p near fet) same (sige or silicon near germanium or gesi or si near ge) same (gate) near5 (high near k or high near dielectric or sin or silicon adj nitride or si adj n or sion or silicon adj oxynitride or alo or alumina or aluminum near oxide or hfo or hafnium near oxide or zro or zirconium near oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or bst or pst or pzn or pmn or metal near oxide or metal near silicate or ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:04
S22	164	(sige or silicon near germanium or gesi or si near ge) same (gate) near2 (oxide or dielectric) near5 (high near k or high near dielectric or sin or silicon adj nitride or si adj n or sion or silicon adj oxynitride or alo or alumina or aluminum near oxide or hfo or hafnium near oxide or zro or zirconium near oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or bst or pst or pzn or pmn or metal near oxide or metal near silicate or ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:34

S23	163	(pmos or pmosfet or p near mos or p near mosfet or p near channel or p near fet) near6 (sige or silicon near germanium or gesi or si near ge) and (nmos or nmosfet or n near mos or n near mosfet or n near channel or n near fet) near6 (strained or strain or straining or tensile) near3 (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:31
S24	11	(pmos or pmosfet or p near mos or p near mosfet or p near channel or p near fet) near8 (gate) near5 (high near k or high near dielectric or sin or silicon adj nitride or si adj n or sion or silicon adj oxynitride or alo or alumina or aluminum near oxide or hfo or hafnium near oxide or zro or zirconium near oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or bst or pst or pzn or pmn or metal near oxide or metal near silicate or ferroelectric) and (nmos or nmosfet or n near mos or n near mosfet or n near channel or n near fet) near8 gate near5 (thermal$3) near (oxide or oxidation or oxidized or oxidizing or oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:06
S25	8	("5155571" | "5847419" | "5970331" | "6255700" | "6310367" | "6339232" | "6455330" | "6475869").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/30 16:23
S26	5	S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:31
S27	1	S23 and S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:34
S28	2	(sige or silicon near germanium or gesi or si near ge) near6 (gate) near5 (high near k or high near dielectric or sin or silicon adj nitride or si adj n or sion or silicon adj oxynitride or alo or alumina or aluminum near oxide or hfo or hafnium near oxide or zro or zirconium near oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or bst or pst or pzn or pmn or metal near oxide or metal near silicate or ferroelectric) and (tensile or strained or strain or straining) near2 (silicon or si) near6 gate near5 (thermal$3 near (oxide or oxidized or oxidation or oxidizing) or sio or silicon near oxide or silicon near dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:46
S29	3	(sige or silicon near germanium or gesi or si near ge) near15 (gate) near5 (high near k or high near dielectric or sin or silicon adj nitride or si adj n or sion or silicon adj oxynitride or alo or alumina or aluminum near oxide or hfo or hafnium near oxide or zro or zirconium near oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or bst or pst or pzn or pmn or metal near oxide or metal near silicate or ferroelectric) and (tensile or strained or strain or straining) near2 (silicon or si) near15 gate near5 (thermal$3 near (oxide or oxidized or oxidation or oxidizing) or sio or silicon near oxide or silicon near dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:54

EAST- interference search

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	18	((nmos or n near mos or n near channel or nmosfet or n near fet or n near mosfet) near8 (strained or strain or tensile or straining) near2 (si or silicon)).clm.	US-PGPUB	OR	ON	2005/12/01 15:00
L2	27	((pmos or p near mos or p near channel or pmosfet or p near fet or p near mosfet) near5 (sige or si near ge or silicon near germanium or gesi)).clm.	US-PGPUB	OR	ON	2005/12/01 15:01
L3	5	L1 and L2	US-PGPUB	OR	ON	2005/12/01 14:59
L4	4	((nmos or n near mos or n near channel or nmosfet or n near fet or n near mosfet) near8 (strained or strain or tensile or straining) near2 (si or silicon) and gate near4 (thermal$3 near oxid$ or sio or silicon near oxide or silicon near dioxide)).clm.	US-PGPUB	OR	ON	2005/12/01 15:00
L5	0	((pmos or p near mos or p near channel or pmosfet or p near fet or p near mosfet) near5 (sige or si near ge or silicon near germanium or gesi) and gate near6 (high near k or high near dielectric or metal near oxide or alo or alumina or aluminum adj oxide or tio or titanium near oxide or tao or tantalum near oxide or wo or tungsten near oxide or zro or zirconium near oxide or hfo or hafnium near oxide)).clm.	US-PGPUB	OR	ON	2005/12/01 15:06
L6	0	((nmos or nmosfet or n near mos or n near mosfet) near8 (pmos or pmosfet or p near mos or p near mosfet) near10 (different or differing or nonuniform or separate or distinct) near4 (gate) near (oxide or dielectric)).clm.	US-PGPUB	OR	ON	2005/12/01 15:03
L7	37	(((nmos or nmosfet or n near mos or n near mosfet) near8 (pmos or pmosfet or p near mos or p near mosfet) or cmos) near5 (balanced or balancing or identical or compensated or "same" or similar or uniform or equivalent or equal) near2 (current or voltage or bias)).clm.	US-PGPUB	OR	ON	2005/12/01 15:04
L8	0	((pmos or p near mos or p near channel or pmosfet or p near fet or p near mosfet) near5 (sige or si near ge or silicon near germanium or gesi) and gate near6 (silicon adj nitride or sin or oxynitride or sion)).clm.	US-PGPUB	OR	ON	2005/12/01 15:06